



#10 IDS
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FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT	ATTY. DOCKET 033035 M 0342	SERIAL NO. 10/691,569
	APPLICANT: Kensaku MOTOKI, et al.	
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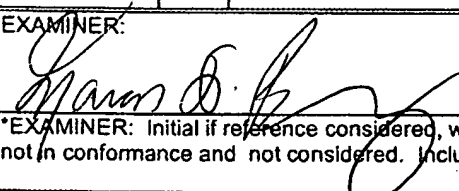
U.S. PATENT DOCUMENTS

*Examiner's Initials		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE, IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

FOREIGN PATENT DOCUMENTS

*Examiner's Initials		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION YES NO	
	AL							
	AM							
	AN							
	AO							
	AP							

OTHER INFORMATION (Including Author, Title, Date, Pertinent Pages, Etc.)

LA	AQ	Nam et al. "Growth of GaN and Al _{0.8} Ga _{0.2} N on Patterened Substrates via Organometallic Vapor Phase Epitaxy" Jpn.j. Appl. Phys. Vol 36 (May 1, 1997), Pt. 2, No. 5A, pg. L532
	AR	
	AS	
EXAMINER: 		DATE CONSIDERED: 2/19/2007
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.		